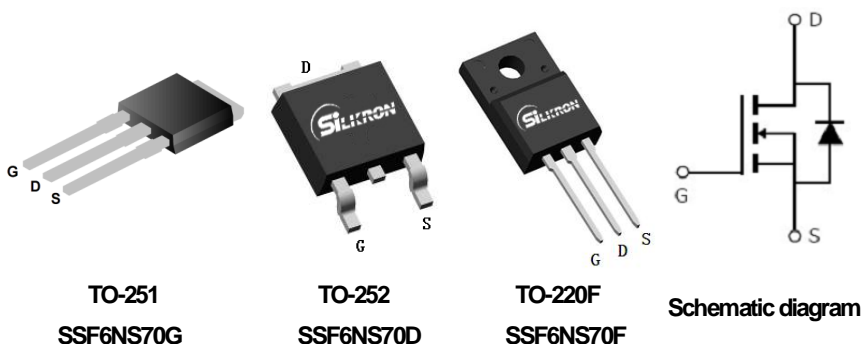


Main Product Characteristics:

V_{DSS}	700V
$R_{DS(on)}$	1.2 Ω (typ.)
I_D	5.2A ①


Features and Benefits:
Features:

- High dv/dt and avalanche capabilities
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance


Description:

The SSF6NS70G/D/F series MOSFETs is a new technology, which combines an innovative technology and advance process. This new technology achieves low Rdson, energy saving, high reliability and uniformity, superior power density and space saving.

Absolute max Rating:

Symbol	Parameter	Max.	Units	
I_D @ TC = 25°C	Continuous Drain Current, V_{GS} @ 10V	5.2 ①	A	
I_D @ TC = 100°C	Continuous Drain Current, V_{GS} @ 10V	3.2①		
I_{DM}	Pulsed Drain Current ②	15.6		
P_D @TC = 25°C	Power Dissipation ③	For TO-251/TO-252 package	50	W
		For TO-220F package	31.2	
	Linear Derating Factor	For TO-251/TO-252 package	0.4	W/°C
		For TO-220F package	0.25	
V_{DS}	Drain-Source Voltage	700	V	
V_{GS}	Gate-to-Source Voltage	± 30	V	
E_{AS}	Single Pulse Avalanche Energy @ L=22.4mH	54	mJ	
I_{AR}	Avalanche Current @ L=22.4mH	2.2	A	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C	

Thermal Resistance

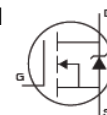
Symbol	Characterizes	Typ.	Max.	Units	
R _{θJC}	Junction-to-case ③	For TO-251/TO-252 package	—	2.5	°C/W
		For TO-220F package	—	4	
R _{θJA}	Junction-to-ambient (t ≤ 10s) ④	For TO-251/TO-252 package	—	75	°C/W
		For TO-220F package	—	80	

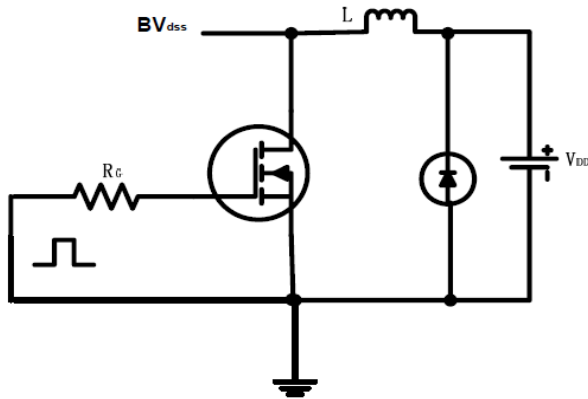
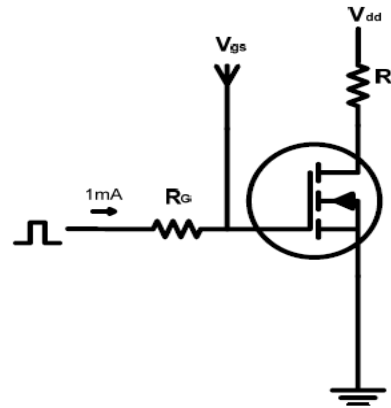
Electrical Characterizes @T_A=25°C unless otherwise specified

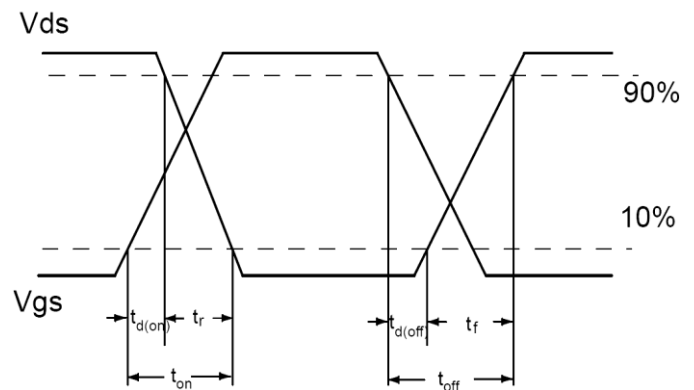
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source breakdown voltage	700	—	—	V	V _{GS} = 0V, I _D = 250μA
R _{DS(on)}	Static Drain-to-Source on-resistance	—	1.2	1.4	Ω	V _{GS} =10V, I _D = 1A
		—	2.9	—		T _J = 125°C
V _{GS(th)}	Gate threshold voltage	2	—	4	V	V _{DS} = V _{GS} , I _D = 250μA
		—	2.8	—		T _J = 125°C
I _{DSS}	Drain-to-Source leakage current	—	—	1	μA	V _{DS} = 700V, V _{GS} = 0V
		—	—	50		T _J = 125°C
I _{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V _{GS} = 30V
		—	—	-100		V _{GS} = -30V
Q _g	Total gate charge	—	8.3	—	nC	I _D = 4A, V _{DS} =100V, V _{GS} = 10V
Q _{gs}	Gate-to-Source charge	—	2.3	—		
Q _{gd}	Gate-to-Drain("Miller") charge	—	2.6	—		
t _{d(on)}	Turn-on delay time	—	10.1	—	ns	V _{GS} =10V, V _{DS} =380V, R _{GEN} =18Ω, I _D =4.5A
t _r	Rise time	—	18.4	—		
t _{d(off)}	Turn-Off delay time	—	16.8	—		
t _f	Fall time	—	14.8	—		
C _{iss}	Input capacitance	—	272	—	pF	V _{GS} = 0V V _{DS} = 25V f = 1MHz
C _{oss}	Output capacitance	—	168	—		
C _{rss}	Reverse transfer capacitance	—	3.14	—		

Source-Drain Ratings and Characteristics

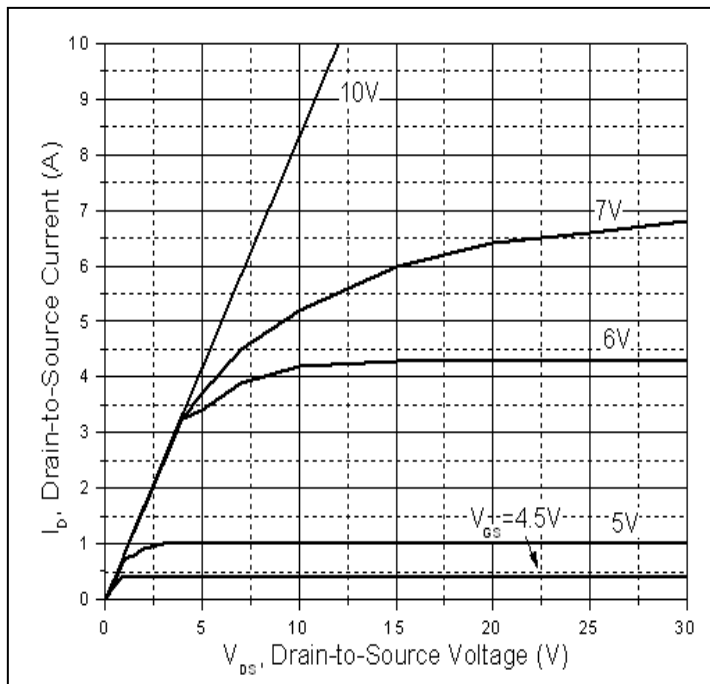
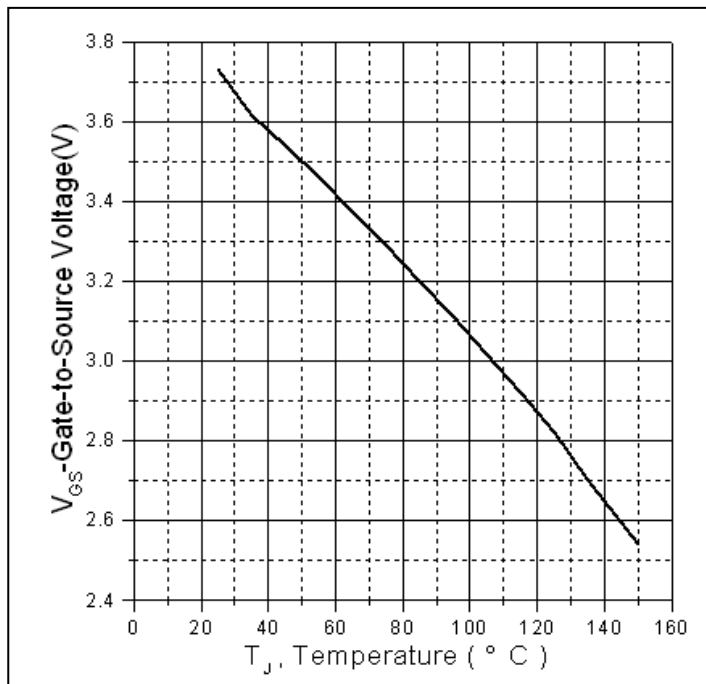
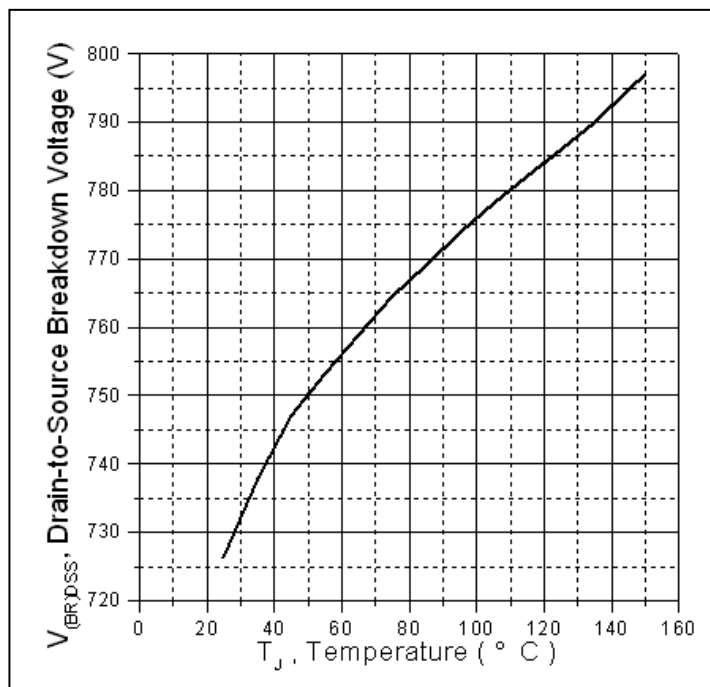
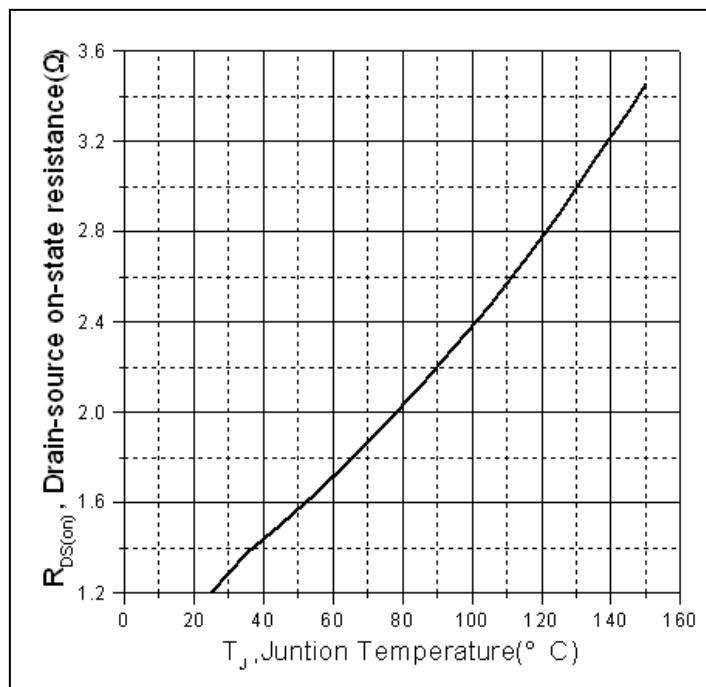
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	5.2 ①	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode)	—	—	15.6	A	
V _{SD}	Diode Forward Voltage	—	0.84	1.2	V	I _S =2.8A, V _{GS} =0V
t _{rr}	Reverse Recovery Time	—	284	—	nS	T _J = 25°C, I _F = I _S ,
Q _{rr}	Reverse Recovery Charge	—	1395	—	nC	di/dt = 100A/μs



Test circuits and Waveforms
EAS test circuits:

Gate charge test circuit:

Switch Time Test Circuit:

Switch Waveforms:

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$

Typical electrical and thermal characteristics

Figure 1: Typical Output Characteristics

Figure 2. Gate to source cut-off voltage

Figure 3. Drain-to-Source Breakdown Voltage Vs. Case Temperature

Figure 4: Normalized On-Resistance Vs. Case Temperature

Typical electrical and thermal characteristics

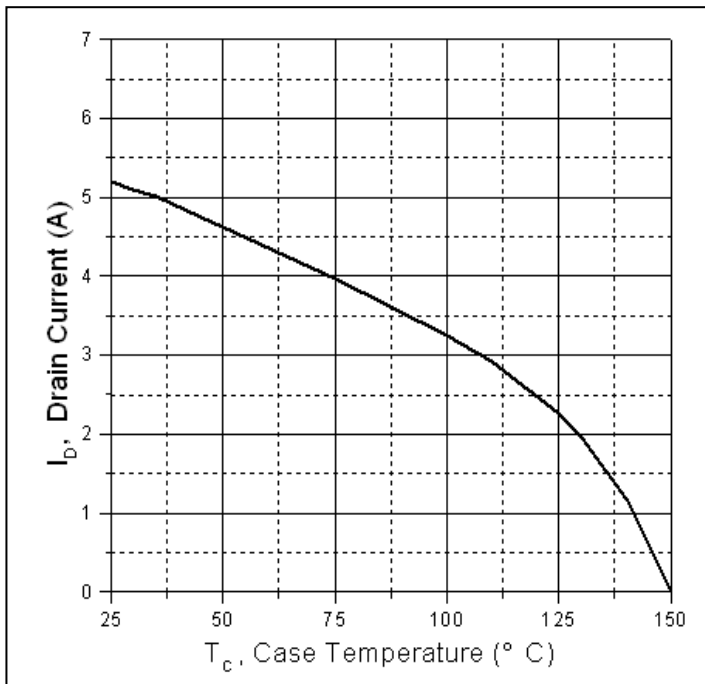


Figure 5. Maximum Drain Current Vs. Case Temperature

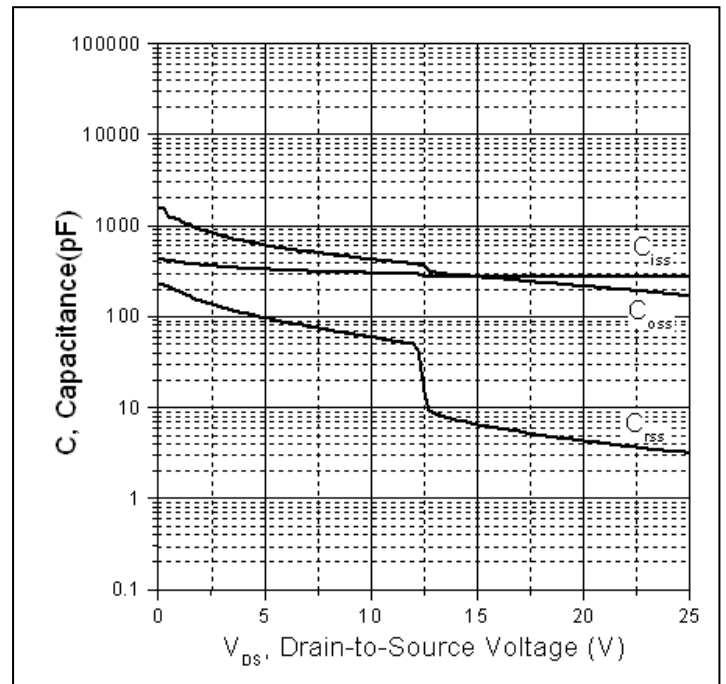
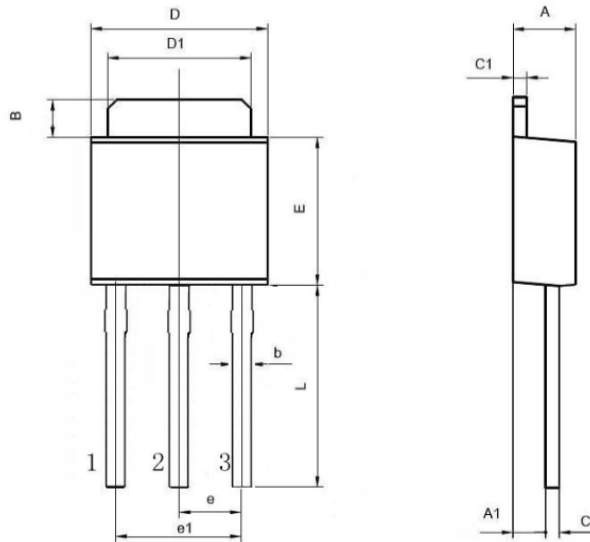
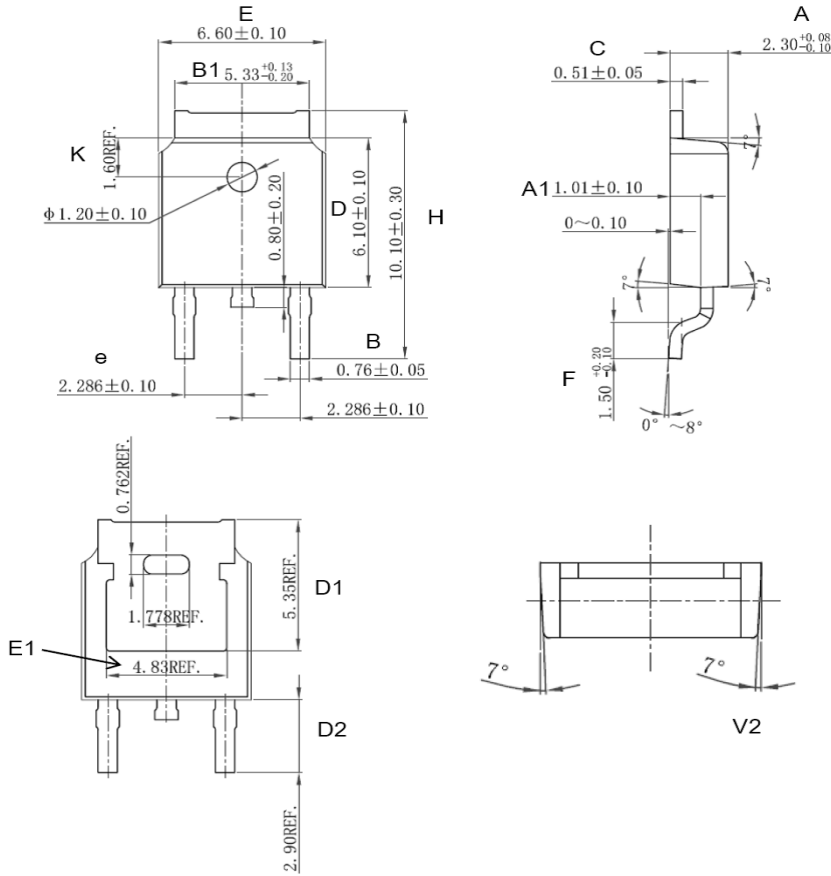


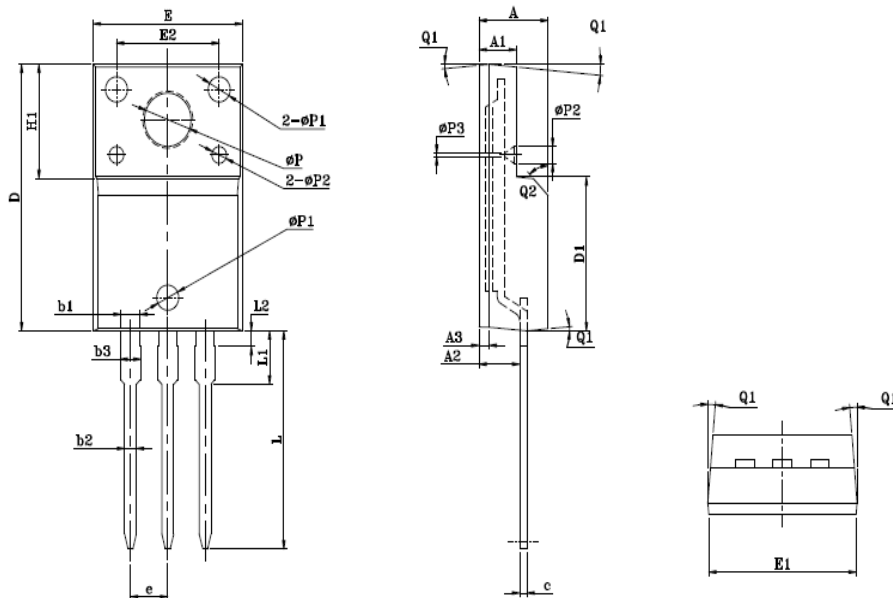
Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

Mechanical Data:
TO-251 PACKAGE OUTLINE DIMENSION


Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	2.200	-	2.400	0.087	-	0.094
A1	0.950	-	1.150	0.037	-	0.045
B	0.950	-	1.250	0.037	-	0.049
b	0.500	-	0.700	0.020	-	0.028
c	0.450	-	0.550	0.018	-	0.022
c1	0.450	-	0.550	0.018	-	0.022
D	6.450	-	6.750	0.254	-	0.266
D1	5.200	-	5.400	0.205	-	0.213
E	5.950	-	6.250	0.234	-	0.246
e	2.240	-	2.340	0.088	-	0.092
e1	4.430	-	4.730	0.174	-	0.186
L	9.000	-	9.400	0.354	-	0.370

TO-252 PACKAGE OUTLINE DIMENSION


Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	2.200	2.300	2.380	0.087	0.091	0.094
A1	0.910	1.010	1.110	0.036	0.040	0.044
B	0.710	0.760	0.810	0.028	0.030	0.032
B1	5.130	5.330	5.460	0.202	0.210	0.215
C	0.460	0.510	0.560	0.018	0.020	0.022
D	6.000	6.100	6.200	0.236	0.240	0.244
D1	5.350 (REF)			0.211 (REF)		
D2	2.900 (REF)			0.114 (REF)		
E	6.500	6.600	6.700	0.256	0.260	0.264
E1	4.83 (REF)			0.190 (REF)		
e	2.186	2.286	2.386	0.086	0.090	0.094
H	9.800	10.100	10.400	0.386	0.398	0.409
F	1.400	1.500	1.700	0.055	0.059	0.067
K	1.600 (REF)			0.063 (REF)		
V2	8° (REF)			8° (REF)		

TO220F PACKAGE OUTLINE DIMENSION_GN


Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
E	9.960	10.160	10.360	0.392	0.400	0.408
E1	9.840	10.040	10.240	0.387	0.395	0.403
E2	6.800	7.000	7.200	0.268	0.276	0.283
A	4.600	4.700	4.800	0.181	0.185	0.189
A1	2.440	2.540	2.640	0.096	0.100	0.104
A2	2.660	2.760	2.860	0.105	0.109	0.113
A3	0.600	0.700	0.800	0.024	0.028	0.031
c	-	0.500	-	-	0.020	-
D	15.780	15.870	15.980	0.621	0.625	0.629
D1	8.970	9.170	9.370	0.353	0.361	0.369
H1	6.500	6.700	6.800	0.256	0.264	0.268
e	2.54BSC			0.10BSC		
φP	3.080	3.180	3.280	0.121	0.125	0.129
φP1	1.400	1.500	1.600	0.055	0.059	0.063
φP2	0.900	1.000	1.100	0.035	0.039	0.043
φP3	0.100	0.200	0.300	0.004	0.008	0.012
L	12.780	12.980	13.180	0.503	0.511	0.519
L1	2.970	3.170	3.370	0.117	0.125	0.133
L2	0.830	0.930	1.030	0.033	0.037	0.041
Q1	3°	5°	7°	3°	5°	7°
Q2	43°	45°	47°	43°	45°	47°
b1	1.180	1.280	1.380	0.046	0.050	0.054
b2	0.760	0.800	0.840	0.030	0.031	0.033
b3	-	-	1.420	-	-	0.056

Ordering and Marking Information
Device Marking: SSF6NS70G/D/F
Package (Available)
TO-251(IPAK)/TO-252(DPAK)/TO-220F
Operating Temperature Range
C : -55 to 150 °C
Devices per Unit

Package Type	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO-251	80	60	4800	5	24000
TO-252	75	48	3600	5	18000
TO-220F	50	20	1000	6	6000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T _j =125°C to 150°C @ 80% of Max V _{DSS} /V _{CES} /VR	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T _j =150°C @ 100% of Max V _{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices

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